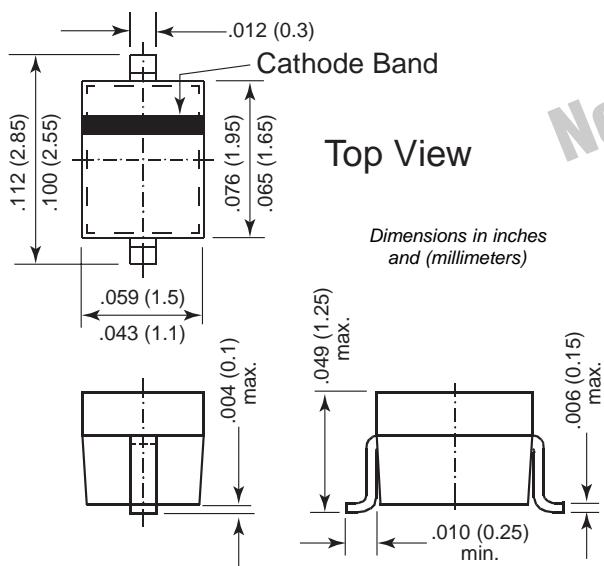
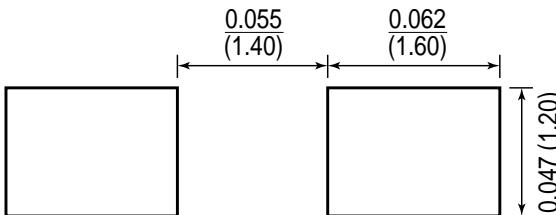



**SOD-323**

**Pad Layout SOD-323**


## Mechanical Data

- Case:** SOD-323 plastic case  
**Weight:** approximately 0.004 grams  
**Marking Code:** S1  
**Packaging Codes/Options:**  
 D5/10K per 13" reel (8mm tape)  
 D6/3K per 7" reel (8mm tape)

## Features

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- Ideal for protection of MOS devices, steering, biasing, and coupling diodes for fast switching and low logic level applications.

## Maximum Ratings and Thermal Characteristics (T<sub>c</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	V <sub>R</sub>	30	V
Forward Current	I <sub>F</sub>	100	mA
Forward Surge Current, t <sub>p</sub> = 10 ms	I <sub>FSM</sub>	0.75	A
Power Dissipation T <sub>c</sub> = 25°C	P <sub>tot</sub>	250 <sup>(1)</sup>	mW
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	500	°C/W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature Range	T <sub>s</sub>	-65 to +150	°C

Note: (1) Valid provided that electrodes are kept at ambient temperature

## Electrical Characteristics (T<sub>j</sub> = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	BVR	I <sub>R</sub> = 100 µA	30	—	—	V
Leakage Current	I <sub>R</sub>	V <sub>R</sub> = 25 V	—	—	1000	nA
Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 2.0 mA	—	300	—	
		I <sub>F</sub> = 15 mA	—	360	—	
		I <sub>F</sub> = 50 mA	—	470	550	mV
		I <sub>F</sub> = 100 mA	—	580	800	
Junction Capacitance	C <sub>tot</sub>	V <sub>R</sub> = 10 V, f = 1.0 MHz	—	—	7.0	pF